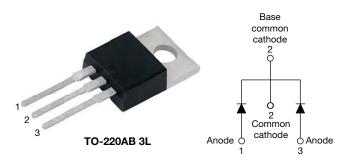
Vishay Semiconductors

Ultrafast Rectifier, 10 A FRED Pt[®]



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SHAY

PRIMARY CHARACTERISTICS						
I _{F(AV)} 2 x 5 A						
V _R	200 V					
V _F at I _F	0.87 V					
t _{rr} typ.	See Recovery table					
T _J max.	175 °C					
Package	TO-220AB 3L					
Circuit configuration	Common cathode					

FEATURES

- · Ultrafast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Designed and qualified according to JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

VS-MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage		V _{RRM}		200	V			
Average restified forward ourrest	per leg	I		5				
Average rectified forward current	total device	IF(AV)	Rated V _R , T _C = 149 °C	10				
Non-repetitive peak surge current per leg		I _{FSM}		50	А			
Peak repetitive forward current per l	eg	I _{FM}	Rated V _R , square wave, 20 kHz $T_{C} = 149 \text{ °C}$	10				
Operating junction and storage temp	peratures	T _J , T _{Stg}		-65 to +175	°C			

ELECTRICAL SPECIFICATIONS PER LEG ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-		
Forward voltage		I _F = 5 A, T _J = 125 °C	-	0.87	0.99	V	
	V _F	I _F = 10 A, T _J = 125 °C	-	1.02	1.20		
		I _F = 10 A	-	1.12	1.25		
Deverse leekege eurrent		$V_{R} = V_{R}$ rated	-	-	10		
Reverse leakage current	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA	
Junction capacitance	CT	V _R = 200 V	-	8	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

Revision: 13-Jan-2022

Document Number: 96199

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VS-MUR1020CT-M3

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 $^{\circ}$ C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µs, V _R = 30 V	-	-	35			
Poverse receiver time	+	I _F = 0.5 A, I _R = 1.0 A, I _{REC} = 0.25 A		-	-	25			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	24	-	ns		
		T _J = 125 °C		-	35	-			
Deals receivers aurrent	I _{RRM}	T _J = 25 °C	$I_F = 5 A$	-	3.3	-	А		
Peak recovery current		T _J = 125 °C	dI _F /dt = 200 A/µs V _B = 160 V	-	5.0	-	A		
Reverse recovery charge	<u> </u>	T _J = 25 °C		-	33	-			
	Q _{rr}	T _J = 125 °C		-	76	-	nC		

THERMAL MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C		
Thermal resistance, junction to case per leg	R _{thJC}		-	-	5			
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	50	°C/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-			
Weight			-	2.0	-	g		
weight			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-220AB 3L		MUR1	020CT			

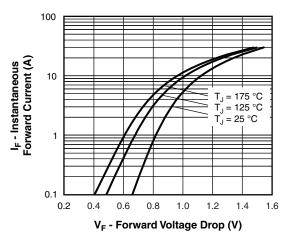


Fig. 1 - Typical Forward Voltage Drop Characteristics

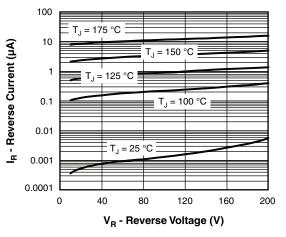


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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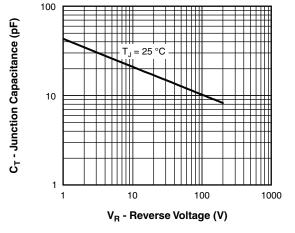


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

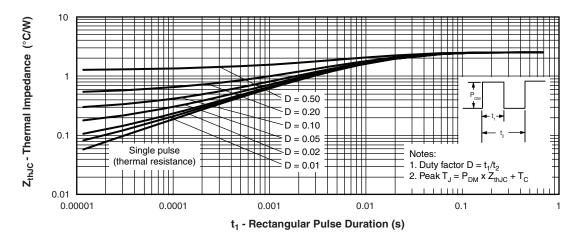


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

Average Power Loss (W)

7

6

5

4

3

2

1

0

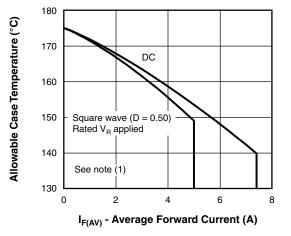
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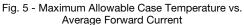
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2 3 4 5 6 7

I_{F(AV)} - Average Forward Current (A)

Fig. 6 - Forward Power Loss Characteristics





Note

(1)

Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}$; Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}/D$) (see fig. 6); Pd_{REV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = Rated V_R

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RMS limit

D = 0.01

D = 0.02

D = 0.05

D = 0.1

D = 0.2

D = 0.5

DC

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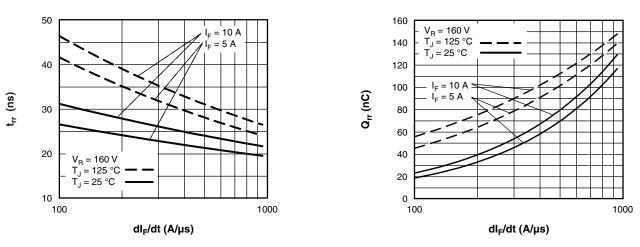


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

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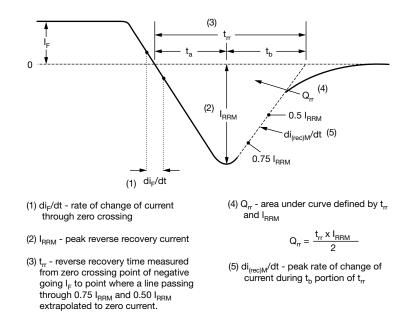


Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device cod

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le	vs-	•	MUR	10	20	СТ	-M3	
			2	3	4	5	6	
	1 2 3 4 5 6	-	Ultr Cur Volt	afast M rent rati age rati = cente	niconduo UR serie ng (10 = ng (20 = r tap (du ntal digit	es : 10 A) : 200 V) ial) 3L T		АВ, D ² PAK (TO-263AB), TO-262AA
I					0		-compli	ant, and termination lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-MUR1020CT-M3	50	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96154
Part marking information	www.vishay.com/doc?95028

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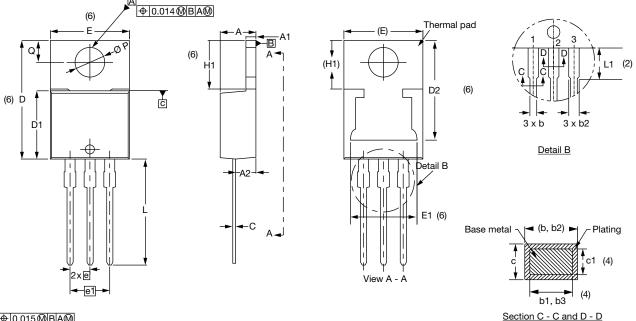
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TO-220AB 3L

DIMENSIONS in millimeters and inches

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⊕0.015@BA@



SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	D 14.85		0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Conforms to JEDEC[®] outline TO-220AB

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimensions: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1
- ⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

Revision: 14-Mar-2022

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Document Number: 96154

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